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Ted Johansson

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21839

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07/17/2002

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EXAMINER

MANDALA, VICTOR A

ART UNIT

PAPER NUMBER

2826

DATE MAILED: 07/17/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No.

09/500,994

Applicant(s)

JOHANSSON ET AL.

Examiner

Victor A Mandala Jr.

Art Unit

2826

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☒ Responsive to communication(s) filed on 04 May 2000.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☒ Claim(s) 1-11 is/are pending in the application.
- 4a) Of the above claim(s) 10 is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-9 and 11 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 09 February 2000 is/are: a) ☐ accepted or b) ☒ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

## Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413) Paper No(s) \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other:

## DETAILED ACTION

### *Drawings*

1. The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the MOS transistor as claimed in claim 9, must be shown or the feature(s) canceled from the claim(s). No new matter should be entered.

A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

### *Claim Rejections - 35 USC § 112*

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

2. Regarding claim 5, the phrase "especially" renders the claim indefinite because it is unclear whether the limitations following the phrase are part of the claimed invention. See MPEP § 2173.05(d).

3. Claim 4 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Referring to claim 4, a semiconductor device, wherein said plug extends deeper into the substrate, (**than therein introduced and/ or existing PN-junctions**). The highlighted section cannot be understood for examining.

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1, 5, 8, and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,240,867 Suzuki et al. in view of U.S. Patent No. 5,583,367 Blossfeld.

4. Referring to claim 1, a semiconductor device arranged at a surface of a semiconductor substrate, (Suzuki et al. Figure 5 #61), having an initial doping, (Suzuki et al. Col. 6 Lines12-13), said device having an electrical connection comprising at least one plug made of a material with a high conductivity, (Suzuki et al. Figure 5 #73), between said initially doped substrate, (Suzuki et al. Figure 5 #61), and said surface of the substrate, (Suzuki et al. Figure 5 #61), said device having at least one ground connection, (Suzuki et al. Figure 5 #100), arranged to be connected to a ground pin, (Suzuki et al. Figure 6A #104), on a package, wherein said at least one ground connection, (Suzuki et al. Figure 5 #100), is arranged to be connected to said ground pin, (Suzuki et al. Figure 6A #104), using said electrical connection, (Suzuki et al. Figure 5 #100), where said substrate, (Suzuki et al. Figure 5 #61), is arranged to be connected to said ground pin, (Suzuki et al. Figure 6A #104), via a reverse side of the substrate, (Suzuki et al. Figure 5 #61), opposite said surface, and thereby being arranged to establish a connection between said ground connection, (Suzuki et al. Figure 5 #100), and said ground pin, (Suzuki et al. Figure 6A #104).

Suzuki et al. does not teach a ground pin and a ground connection but does teach a voltage source pin and connection, (Col. 7 lines 56-60). Suzuki et al. does not specify if the source voltage is a ground or a positive source voltage.

Blossfeld does teach where said substrate, (Blossfeld Figure 1 #2), is arranged to be connected to said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), via a reverse side of the substrate, (Blossfeld Figure 1 #2), opposite said surface, and thereby being arranged to establish a connection between said ground connection, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), and said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48).

I would be obvious to one skilled in the art to combine the teachings of Suzuki et al. and the teachings of Blossfeld because if a required source voltage would be ground it would be obvious to provide it to the semiconductor chip. Suzuki et al. and Blossfeld teaches the same type of substrate interconnect, but Suzuki et al. does not specifically state that the needed voltage is ground it would be obvious to apply ground through the same structure as Blossfeld teaches.

5. Referring to claim 5, a semiconductor device, (Suzuki et al. Figure 5), wherein the upper end of each plug, (73), is connected to said ground connection, (79), via an electrically conductive material, (Col. 9 Line 41), especially a material with a high conductivity, especially a material with a high conductivity, especially a metal material, (Col. 9 Line 41).

Suzuki et al. does not teach a ground connection but does teach a voltage source pin and connection, (Col. 7 lines 56-60). Suzuki et al. does not specify if the source voltage is a ground or a positive source voltage.

Blossfeld does teach where said substrate, (Blossfeld Figure 1 #2), is arranged to be connected to said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), via a reverse side of

the substrate, (Blossfeld Figure 1 #2), opposite said surface, and thereby being arranged to establish a connection between said ground connection, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), and said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48).

It would be obvious to one skilled in the art to combine the teachings of Suzuki et al. and the teachings of Blossfeld because if a required source voltage would be ground it would be obvious to provide it to the semiconductor chip. Suzuki et al. and Blossfeld teaches the same type of substrate interconnect, but Suzuki et al. does not specifically state that the needed voltage is ground it would be obvious to apply ground through the same structure as Blossfeld teaches.

6. Referring to claim 8, a semiconductor device, wherein device is a bipolar transistor and said ground connection is an emitter connection.

Suzuki et al. teaches a bipolar transistor in the claimed package. It would be obvious to one skilled in the art to combine the teachings of Suzuki et al., Blossfeld, and the teachings of D'Anna because the semiconductor structure allows the substrate to be used as an electrical connection, which allows the device to effectively use all of the device and allow the package to be smaller.

7. Referring to claim 11, a semiconductor integrated circuit mounted in a package, said package having a plurality of pins, (Suzuki et al. Figure 6A #107), connecting to the semiconductor circuit, (Suzuki et al. Figure 6A #60), and said circuit having a plurality of semiconductor devices, (Suzuki et al. Figure 5 #65, #68, and #67 which form a transistor and #61 and #63 which form a diode), wherein at least one of said semiconductor devices is a semiconductor device arranged at a surface of a semiconductor substrate having an initial doping, (Suzuki et al. Figure 5 #61), said device having an electrical connection comprising at

least one plug made of a material with high conductivity, (Suzuki et al. Figure 5 #73), between said initially doped substrate, (Suzuki et al. Figure 5 #61), and said surface of the substrate, (Suzuki et al. Figure 5 #61), said device having at least one ground connection, (Suzuki et al. Figure 5 #100), arranged to be connected to a ground pin, (Suzuki et al. Figure 6A #104), on a package, (Suzuki et al. Figure 6A #101), wherein at least one ground connection, (Suzuki et al. Figure 5 #100), is arranged to be connected to said ground pin, (Suzuki et al. Figure 6A #104), using said electrical connection, (Suzuki et al. Figure 5 #100), where said substrate, (Suzuki et al. Figure 5 #61), is arranged to be connected to said ground pin, (Suzuki et al. Figure 6A #104), via a reverse side of the substrate, (Suzuki et al. Figure 5 #61), opposite said surface, and thereby being arranged to establish a connection between said ground connection, (Suzuki et al. Figure 5 #100), and said ground pin, (Suzuki et al. Figure 6A #104).

Suzuki et al. does not teach a ground pin and a ground connection but does teach a voltage source pin and connection, (Col. 7 lines 56-60). Suzuki et al. does not specify if the source voltage is a ground or a positive source voltage.

Blossfeld does teach where said substrate, (Blossfeld Figure 1 #2), is arranged to be connected to said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), via a reverse side of the substrate, (Blossfeld Figure 1 #2), opposite said surface, and thereby being arranged to establish a connection between said ground connection, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48), and said ground pin, (Blossfeld Figure 1 #3 & Col. 2 Lines 46-48).

It would be obvious to one skilled in the art to combine the teachings of Suzuki et al. and the teachings of Blossfeld because if a required source voltage would be ground it would be obvious to provide it to the semiconductor chip. Suzuki et al. and Blossfeld teaches the same

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type of substrate interconnect, but Suzuki et al. does not specifically state that the needed voltage is ground it would be obvious to apply ground through the same structure as Blossfeld teaches.

Claims 2-3, 6-7, and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 5,240,867 Suzuki et al. in view of U.S. Patent No. 5,583,367 Blossfeld. In further view of U.S. Patent No. 6,063,678 D'Anna.

8. Referring to claim 2, a semiconductor device, wherein said material is of another type than the substrate.

Suzuki et al. does teach the substrate to be made of silicon, (Col. 9 Lines 50-55), and the plug material to be made of a polysilicon, (Col. 10 Line 38).

D'Anna also teaches the substrate to be made of silicon, (Col. 7 Line 16), and the plug material to be made of a metal or a silicide, (Figure 17 #222 & Col. 6 Lines 63-67).

It would be obvious to one skilled in the art to combine the teachings of Suzuki et al., Blossfeld, and the teachings of D'Anna because it is well known in the art that metal is a highly conductive material, which would allow a efficient electrical connection between the substrate and an electrode.

9. Referring to claim 3, a semiconductor device, wherein said at least one plug is a metal plug.

D'Anna also teaches the substrate to be made of silicon, (Col. 7 Line 16), and the plug material to be made of a metal or a silicide, (Figure 17 #222 & Col. 6 Lines 63-67).



It would be obvious to one skilled in the art to combine the teachings of Suzuki et al., Blossfeld, and the teachings of D'Anna because it is well known in the art that metal is a highly conductive material, which would allow a efficient electrical connection between the substrate and an electrode.

10. Referring to claim 6, a semiconductor device, wherein said semiconductor device is a high frequency device.

Suzuki et al. does not teach a high frequency device, but D'Anna does, (Col. 3 Lines 16-19). It would be obvious to one skilled in the art to combine the teachings of Suzuki et al., Blossfeld, and the teachings of D'Anna because the semiconductor structure allows the substrate to be used as an electrical connection, which allows the device to effectively use all of the device and allow the package to be smaller.

11. Referring to claim 7, a semiconductor device, wherein said device is a power device, (D'Anna Col. 1 Lines 20-26, and 36-39).

Suzuki et al. does not teach a power device, but D'Anna does, (Col. 1 Lines 20-26, and 36-39). It would be obvious to one skilled in the art to combine the teachings of Suzuki et al., Blossfeld, and the teachings of D'Anna because the semiconductor structure allows the substrate to be used as an electrical connection, which allows the device to effectively use all of the device and allow the package to be smaller.

12. Referring to claim 9, a semiconductor device, wherein said transistor is a MOS transistor and said ground connection is a source connection, (D'Anna Col. 1 Lines 42- 46).

Suzuki et al. does not teach a MOS device, but D'Anna does, (D'Anna Col. 1 Lines 42-46). It would be obvious to one skilled in the art to combine the teachings of Suzuki et al.,

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Blossfeld, and the teachings of D'Anna because the semiconductor structure allows the substrate to be used as an electrical connection, which allows the device to effectively use all of the device and allow the package to be smaller.

*Conclusion*

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Victor A Mandala Jr. whose telephone number is (703) 308-6560. The examiner can normally be reached on Monday through Thursday from 8 am till 6pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

VAMJ  
July 8, 2002

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